

# MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

## BAS16W

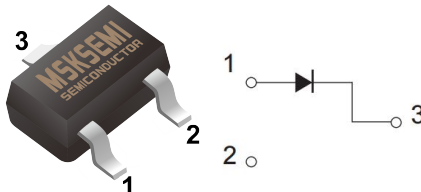

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Product specification

## FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

## Reference News

PACKAGE OUTLINE	MARKING
 <p>SOT-323</p>	

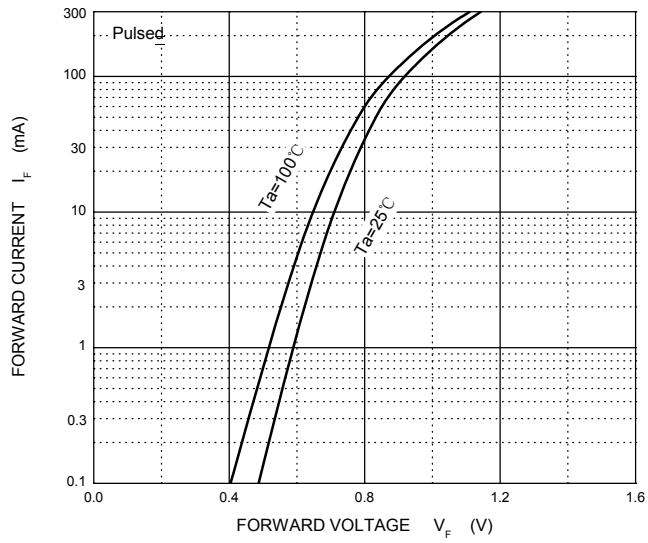
## Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	$V_{RM}$	100	V
Peak Repetitive Peak Reverse Voltage	$V_{RRM}$	75	V
Working Peak Reverse Voltage	$V_{RWM}$		
DC Blocking Voltage	$V_R$		
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	$I_{FM}$	300	mA
Average Rectified Output Current	$I_O$	150	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	$I_{FSM}$	2.0	A
Power Dissipation	$P_d$	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	°C/W
Operation Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	°C

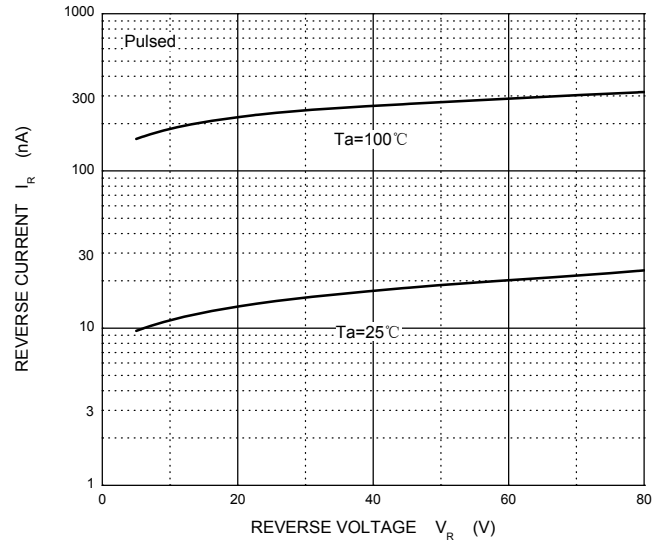
## Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	$V_{(BR)}$	75			V	$I_R=10\mu A$
Forward voltage	$V_{F1}$			0.715	V	$I_F=1mA$
	$V_{F2}$			0.855	V	$I_F=10mA$
	$V_{F3}$			1.0	V	$I_F=50mA$
	$V_{F4}$			1.25	V	$I_F=150mA$
Reverse current	$I_{R1}$			1	$\mu A$	$V_R=75V$
	$I_{R2}$			25	nA	$V_R=20V$
Capacitance between terminals	$C_T$			2	pF	$V_R=0V, f=1MHz$
Reverse recovery time	$t_{rr}$			4	ns	$I_F=I_R=10mA$ $I_{rr}=0.1I_R, R_L=100\Omega$

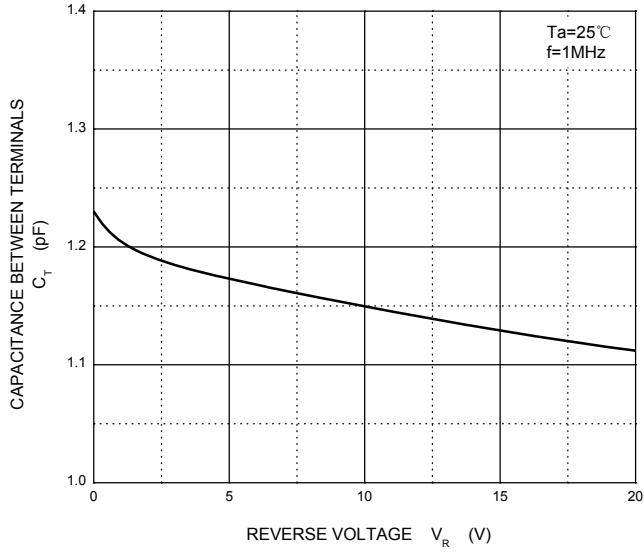
**Forward Characteristics**



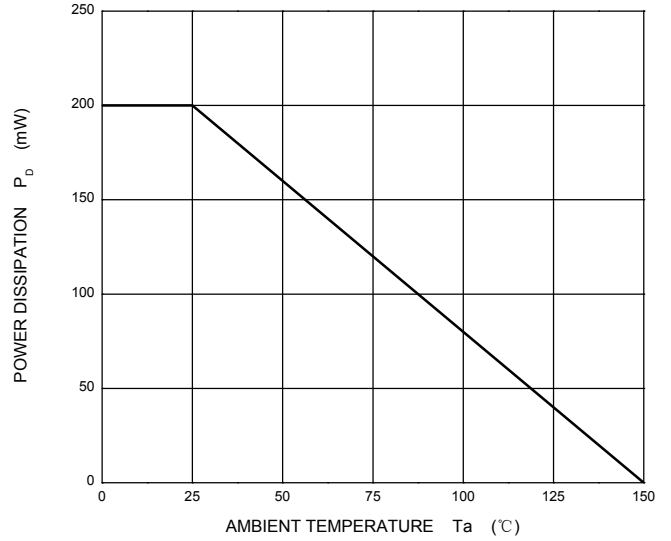
**Reverse Characteristics**



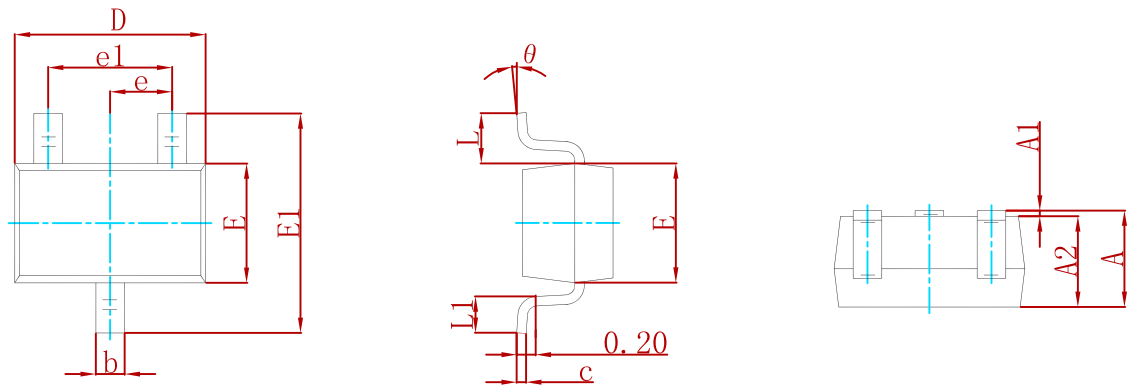
**Capacitance Characteristics**



**Power Derating Curve**

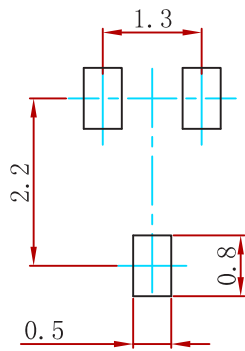


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:  
1.Controlling dimension:in millimeters.  
2.General tolerance:±0.05mm.  
3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BAS16W	SOT-323	3000

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